N-Channel Enhancement Mode Power MOSFET

Description

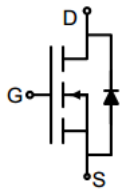
The G08N02L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

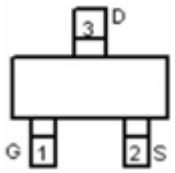
- V_{DS} 20V
- I_D (at V_{GS} = 10V) 8A
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 12.3mΩ
- $R_{DS(ON)}$ (at V_{GS} = 2.5V) < 13.7mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

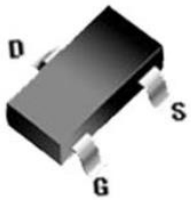
- Power switch
- DC/DC converters



Schematic Diagram



Marking and pin assignment



SOT-23-3L

Device	Package	Marking	Packaging
G08N02L	SOT-23-3L	G08N02	3000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Continuous Drain Current	I_D	8	A
Pulsed Drain Current (note1)	I_{DM}	32	A
Gate-Source Voltage	V_{GS}	±12	V
Power Dissipation	P_D	1.5	W
Single pulse avalanche energy （note3）	E_{AS}	64	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

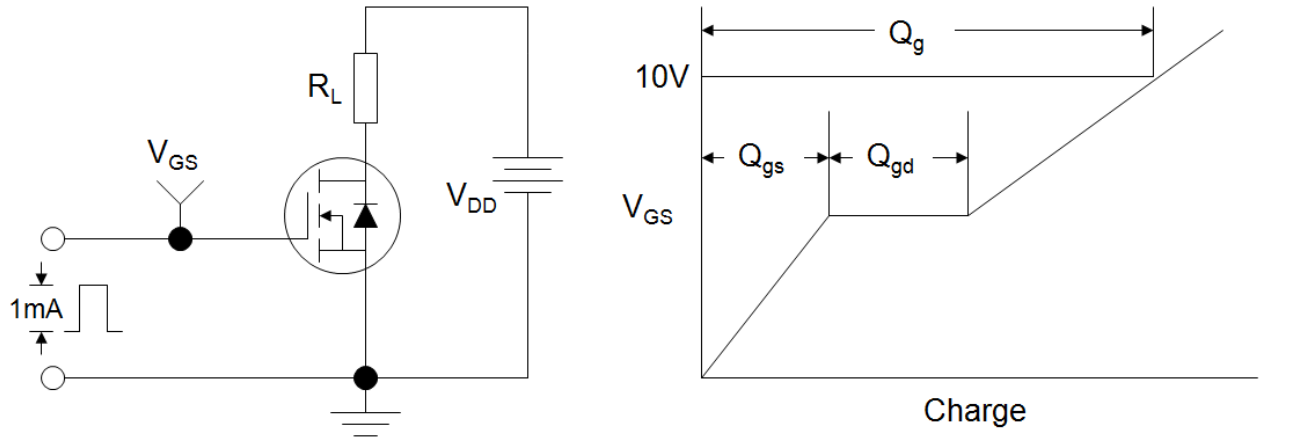
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	83	ºC/W

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	20	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±12V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	0.5	0.64	0.9	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 12A	--	10	12.3	mΩ
		V_{GS} = 2.5V, I_D = 12A	--	11	13.7	
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=4A	--	38	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 10V, f = 1.0MHz	--	929	--	pF
Output Capacitance	C_{oss}		--	163	--	
Reverse Transfer Capacitance	C_{rss}		--	124	--	
Total Gate Charge	Q_g	V_{DS} = 10V, I_D = 8A, V_{GS} = 10V	--	22	--	nC
Gate-Source Charge	Q_{gs}		--	3.8	--	
Gate-Drain Charge	Q_{gd}		--	4.6	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 10V, I_D = 5A, R_G = 50Ω	--	320	--	ns
Turn-on Rise Time	t_r		--	1100	--	
Turn-off Delay Time	$t_{d(off)}$		--	4050	--	
Turn-off Fall Time	t_f		--	2600	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	8	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 1A, V_{GS} = 0V	--	--	1.2	V

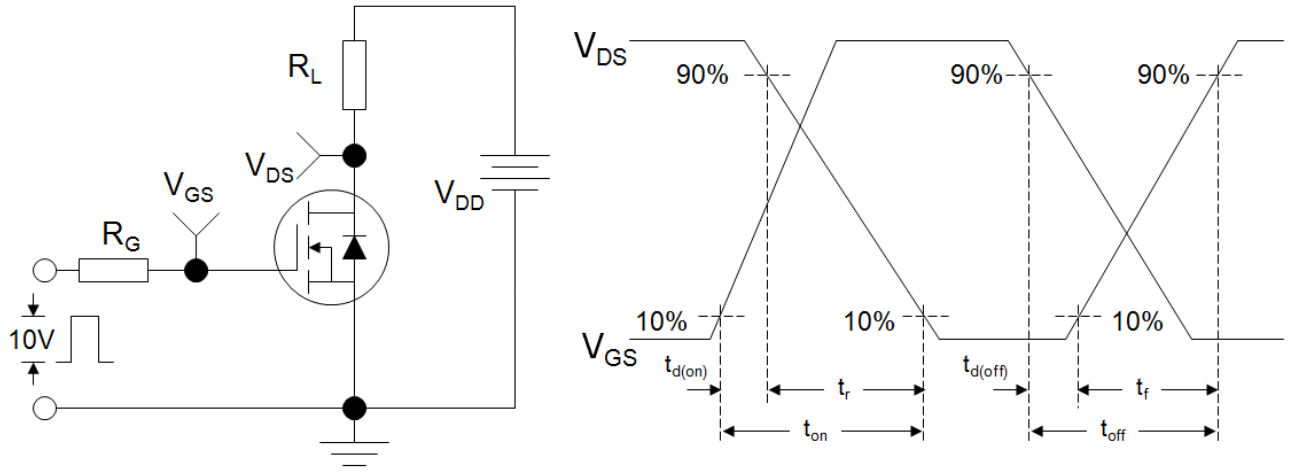
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : Tj=25℃ ,VDD=20V,VG=10V,L=0.5mH,Rg=25Ω

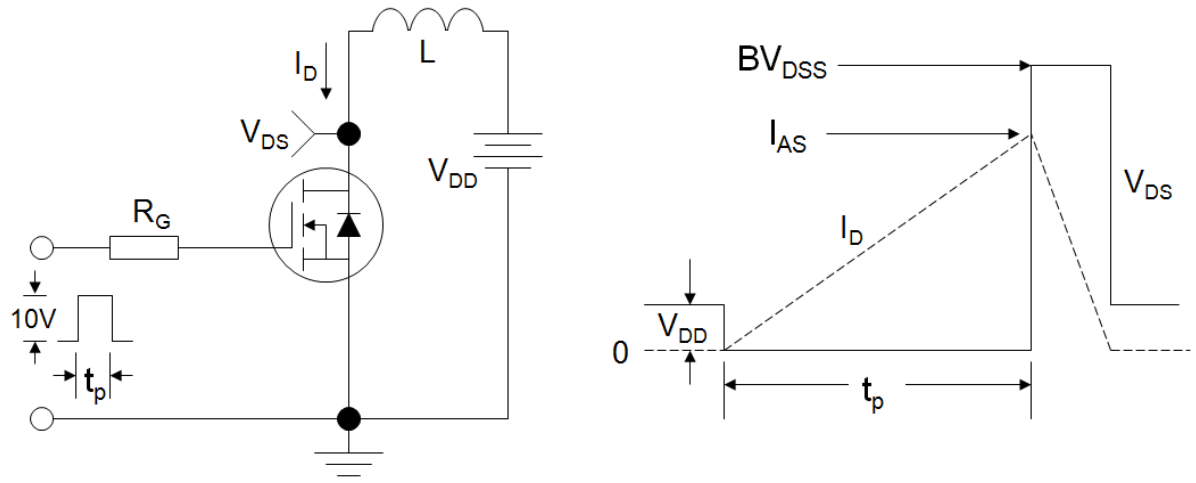
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

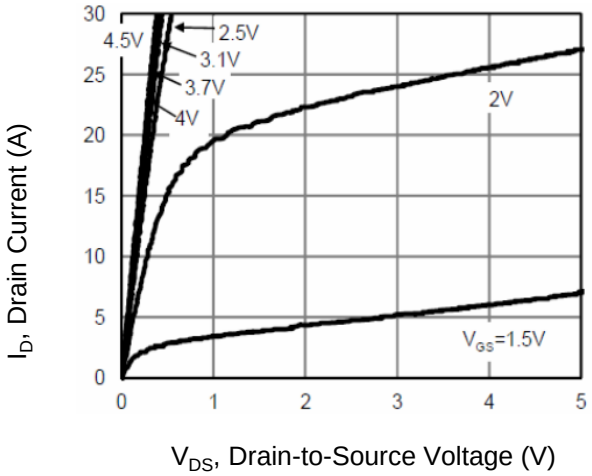


Figure 2. Transfer Characteristics

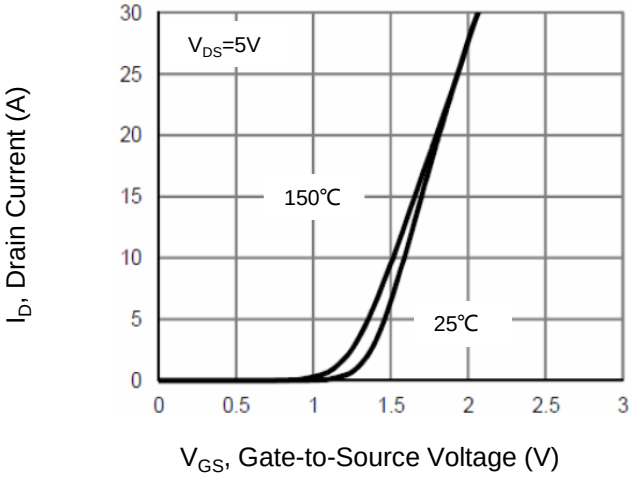


Figure 3. Gate Charge

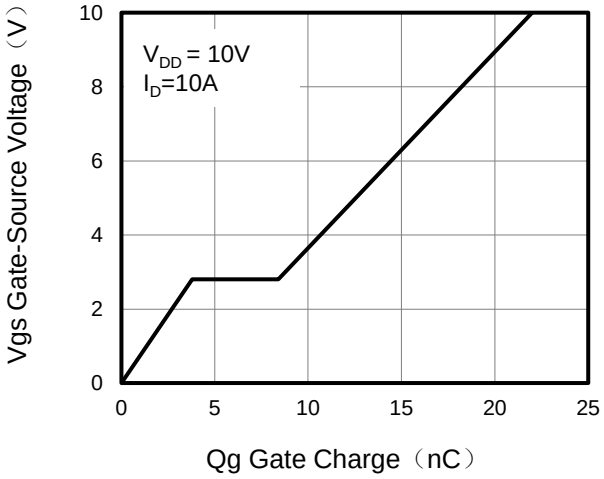


Figure 4. Drain Source On Resistance

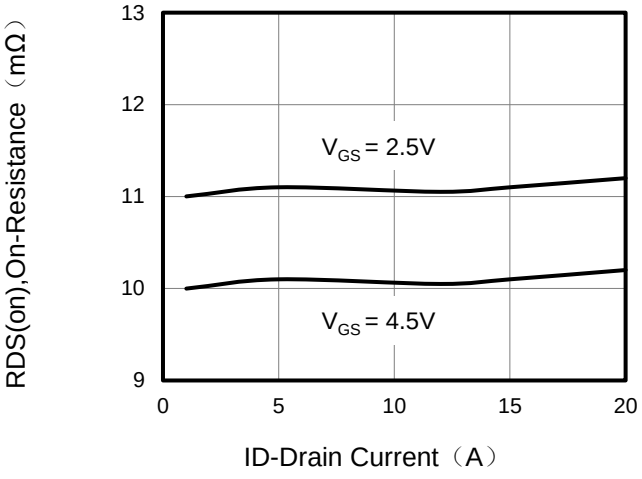


Figure 5. Capacitance vs Vds

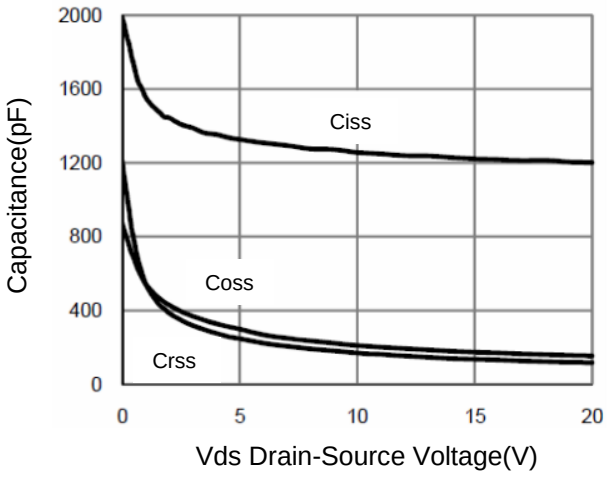
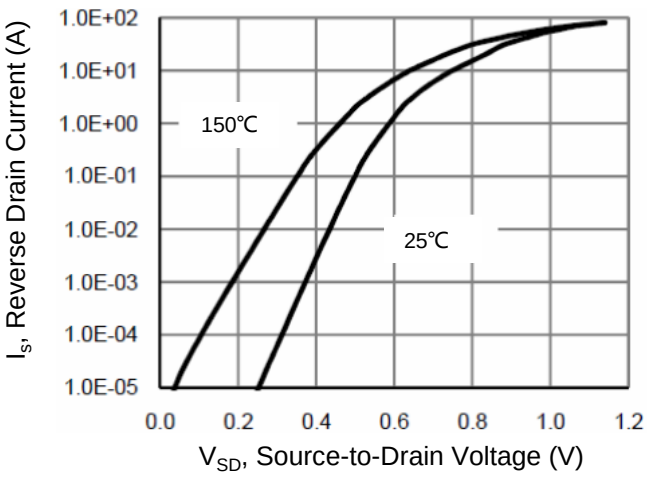


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

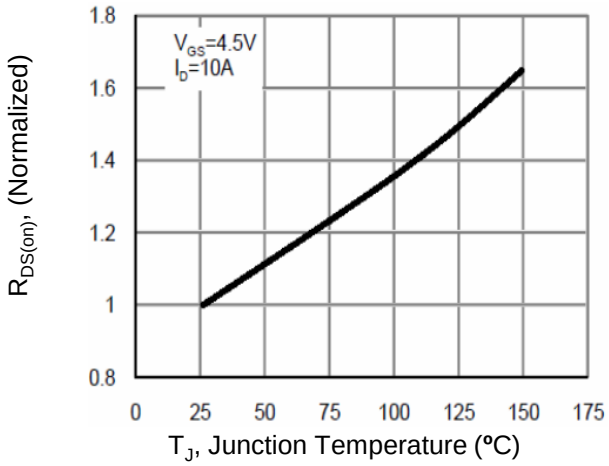


Figure 8. Safe Operation Area

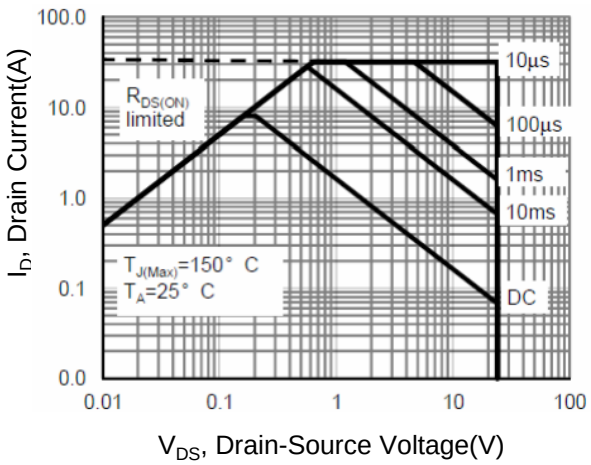
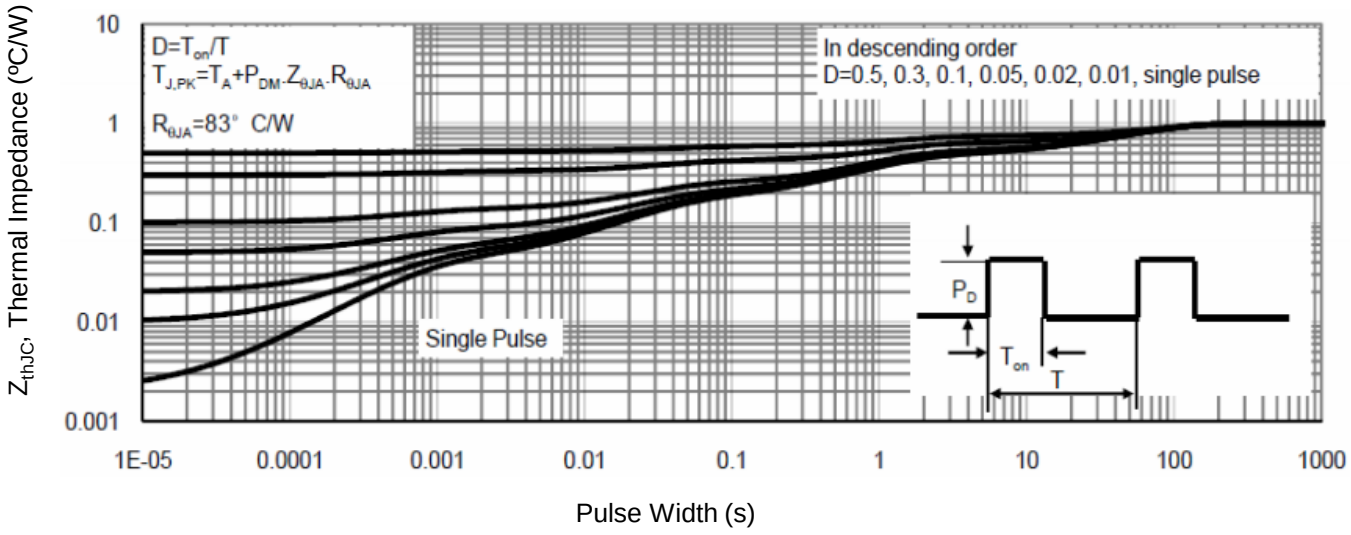
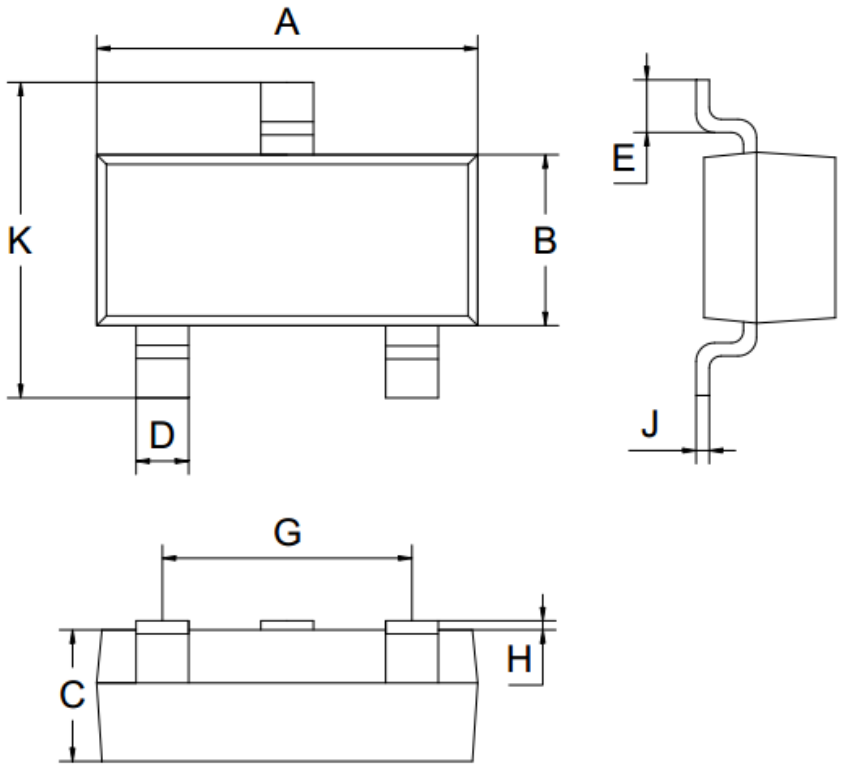


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	2.80	2.90	3.00
B	1.50	1.60	1.70
C	1.00	1.10	1.20
D	0.30	0.40	0.50
E	0.25	0.40	0.55
G	1.90		
H	0.00	-	0.10
J	0.047	0.127	0.207
K	2.60	2.80	3.00
All Dimensions in mm			